

EAST - [jlg.wsp:1]

File View Edit Tools Window Help

12: (16657) 1 and gate.clm.
13: (6379) 2 and flash
14: (5286) 3 and (floating or control).clm.
15: (4423) 4 and (tunnel or oxide)
16: (2494) 5 and dielectric
17: (1363) 6 and oxidation
18: (13) 7 and (dry adj oxidis5)
19: (7) 8 and ((sidewall\$1) or (side adj wall\$1))
110: (0) 5 and C\$1H\$1C1\$1
111: (20) 5 and (dry adj oxidis4)
112: (13) 11 and (sidewall or (side adj wall))

USPAT:USPGPUB
Default operator: OR
Highlight all hit terms initially

11 and (sidewall or (side adj wall))

DRS term RAR term Image Text HTML

	V	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	J	%	Images
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040004094 A1	20040108	48	Semiconductor integrated circuit and nonvolatile memory	365/222			Shukuri, Shoji et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2004
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020106859 A1	20020808		Method of fabricating nonvolatile semiconductor me	438/264			Odake, Yoshinori et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	
3	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020079533 A1	20020627	12	Semiconductor memory device and its manufacture	257/315	257/E29.129; 257/E29.306		Horiguchi, Naoto et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2002
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20020019100 A1	20020214	53	METHOD FOR MANUFACTURING SEMICONDUCTOR INTEGRATED CIR	438/275	257/E21.625; 257/E21.632		SHUKURI, SHOJI et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2002
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20020014641 A1	20020207	53	Semiconductor integrated circuit device and having de	257/275	257/E21.625; 257/E21.632		Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2002
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20020009851 A1	20020124	52	Method for manufacturing semiconductor integrated cir	438/257	257/E21.625; 257/E21.632		Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2002
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20020006054 A1	20020117	51	Semiconductor integrated circuit and nonvolatile memo	365/145			Shukuri, Shoji et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 2002
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6614684 B1	20030902	48	Semiconductor integrated circuit and nonvolatile memo	365/185.05	257/318; 365/185.08		Shukuri, Shoji et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6559012 B2	20030506	51	Method for manufacturing semiconductor integrated cir	438/275	257/E21.625; 257/E21.632		Shukuri, Shoji et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6528839 B2	20030304	50	Semiconductor integrated circuit and nonvolatile memo	257/314	257/315; 257/316		Shukuri, Shoji et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6207991 B1	20010327	16	Integrated non-volatile and CMOS memories having substan	257/326	257/E21.635; 257/E21.639		Rahim, Irfan	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6124157 A	20000926	16	Integrated non-volatile and random access memory and met	438/201	257/E21.552; 257/E21.609		Rahim, Irfan	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6
13	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5976927 A	19991102	10	Two mask method for reducing field oxide encroachment in	438/239	257/E21.552; 257/E21.646		Hsieh, Chia-Ta et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5

Ready NUM